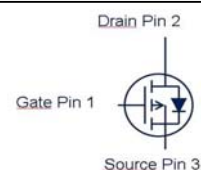
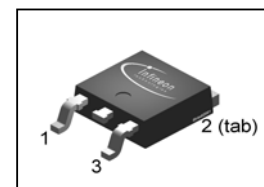


SIPMOS® Power-Transistor
Features

- P-Channel
- Enhancement mode
- Normal level
- Avalanche rated
- Pb-free lead plating; RoHS compliant
- ° Qualified according to AEC Q101

Product Summary

V_{DS}	-100	V
$R_{DS(on),max}$	1	Ω
I_D	-4	A


PG-TO252-3


Type	Package	Marking	Lead free	Packing	Tape and reel information
SPD04P10P G	PG-TO252-3	04P10P	Yes	Non dry	1000 pcs / reel

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$T_C=25\text{ °C}$	-4	A
		$T_C=100\text{ °C}$	-2.8	
Pulsed drain current	$I_{D,pulse}$	$V_{GS}=-10\text{ V}, I_D=-2.8\text{ A}$	-16	
Avalanche energy, single pulse	E_{AS}	$I_D=-4\text{ A}, R_{GS}=25\ \Omega$	57	mJ
Gate source voltage	V_{GS}		± 20	V
Power dissipation	P_{tot}	$T_C=25\text{ °C}$	38	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 175	$^{\circ}\text{C}$
ESD class		JESD22-A114-HBM	1A (250 V to 500 V)	
Soldering temperature			260 $^{\circ}\text{C}$	
IEC climatic category; DIN IEC 68-1			55/175/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - soldering point	R_{thJC}		-	-	3.9	K/W
Thermal resistance, junction - ambient	R_{thJA}	minimal footprint, steady state	-	-	75	
		6 cm ² cooling area ¹⁾ , steady state	-	-	50	

Electrical characteristics, at $T_j=25\text{ }^\circ\text{C}$, unless otherwise specified
Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=-250\text{ }\mu\text{A}$	-100	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-380\text{ }\mu\text{A}$	-2.1	-3.0	-4	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=-100\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ }^\circ\text{C}$	-	-0.1	-1	μA
		$V_{DS}=-100\text{ V}, V_{GS}=0\text{ V}, T_j=150\text{ }^\circ\text{C}$	-	-10	-100	
Gate-source leakage current	I_{GSS}	$V_{GS}=-20\text{ V}, V_{DS}=0\text{ V}$	-	-10	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=-10\text{ V}, I_D=-2.8\text{ A}$	-	644	1000	m Ω
Transconductance	g_{fs}	$ V_{DS} >2 I_D R_{DS(on)max}, I_D=-2.8\text{ A}$	1.2	2.4	-	S

¹⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=-25\text{ V},$ $f=1\text{ MHz}$	-	240	319	pF
Output capacitance	C_{oss}		-	62	82	
Reverse transfer capacitance	C_{rss}		-	28	42	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=-50\text{ V}, V_{GS}=-$ $10\text{ V}, I_D=-4\text{ A}, R_G=6\ \Omega$	-	5.7	8.6	ns
Rise time	t_r		-	8.6	13	
Turn-off delay time	$t_{d(off)}$		-	14	21	
Fall time	t_f		-	4.5	6.8	

Gate Charge Characteristics²⁾

Gate to source charge	Q_{gs}	$V_{DD}=-80\text{ V}, I_D=-4\text{ A},$ $V_{GS}=0\text{ to }-10\text{ V}$	-	1.4	1.8	nC
Gate to drain charge	Q_{gd}		-	5	7	
Gate charge total	Q_g		-	9	12	
Gate plateau voltage	$V_{plateau}$		-	6	-	

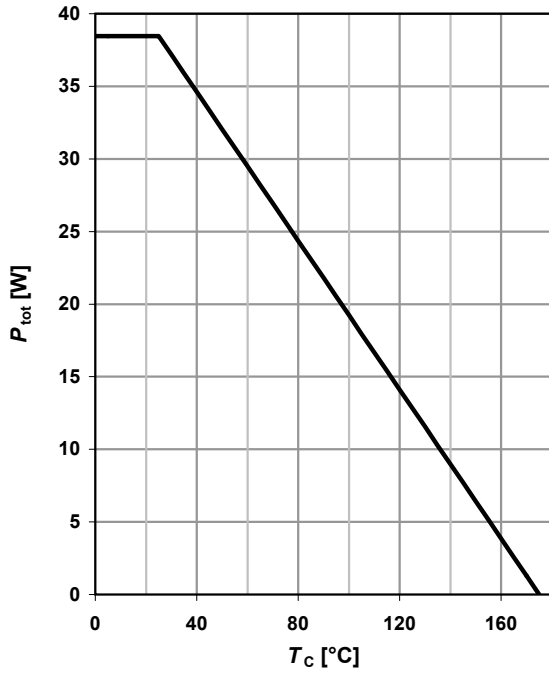
Reverse Diode

Diode continuous forward current	I_S	$T_C=25\text{ }^\circ\text{C}$	-	-	-4.0	A
Diode pulse current	$I_{S,pulse}$		-	-	16.0	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=-4\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	-0.8	-1.2	V
Reverse recovery time	t_{rr}	$V_R=50\text{ V}, I_F= I_S ,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	74	93	ns
Reverse recovery charge	Q_{rr}		-	218	273	nC

²⁾ See figure 16 for gate charge parameter definition

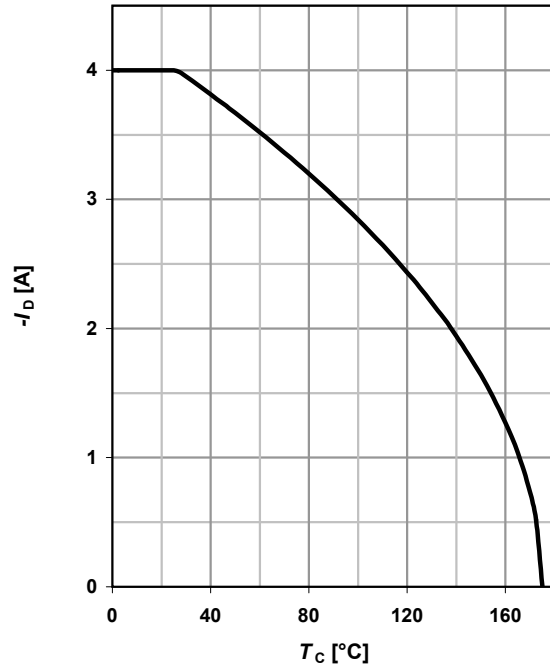
1 Power dissipation

$$P_{tot} = f(T_c)$$



2 Drain current

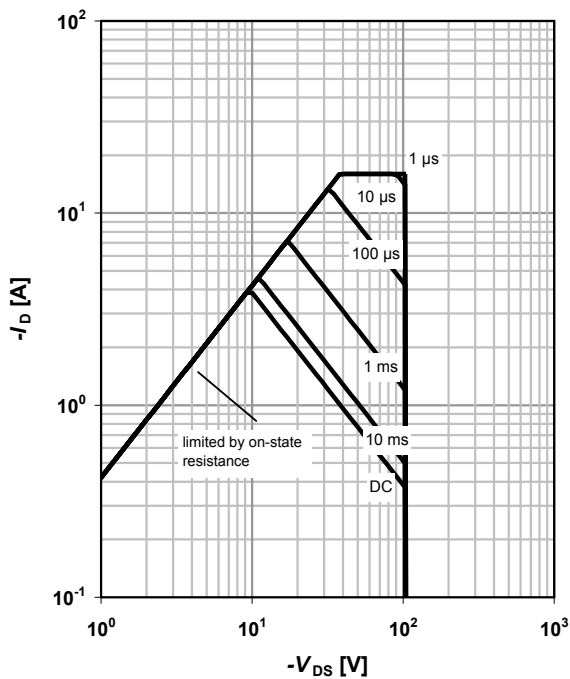
$$I_D = f(T_c); |V_{GS}| \geq 10 \text{ V}$$



3 Safe operating area

$$I_D = f(V_{DS}); T_c = 25 \text{ °C}; D = 0$$

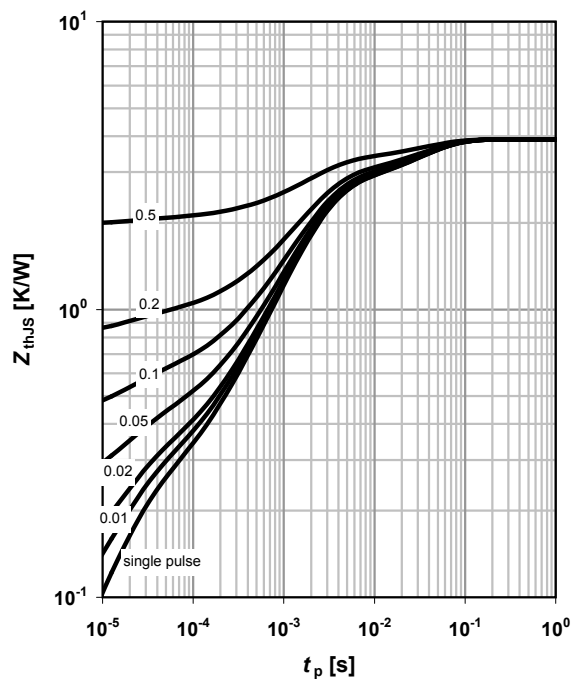
parameter: t_p



4 Max. transient thermal impedance

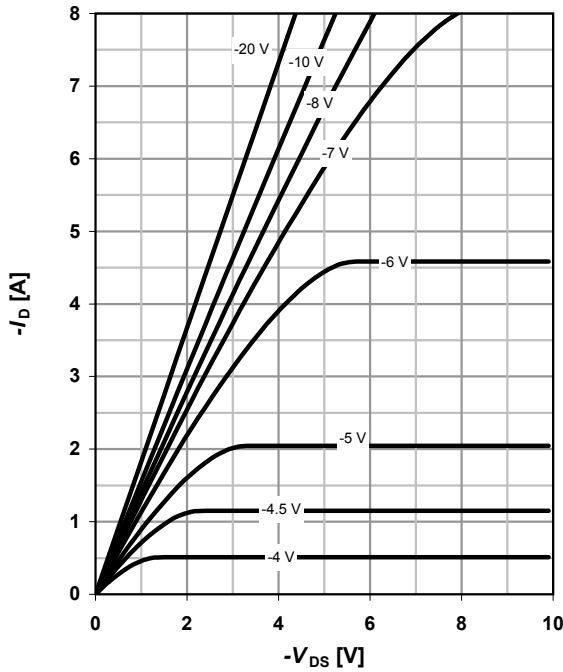
$$Z_{thJC} = f(t_p)$$

parameter: $D = t_p/T$

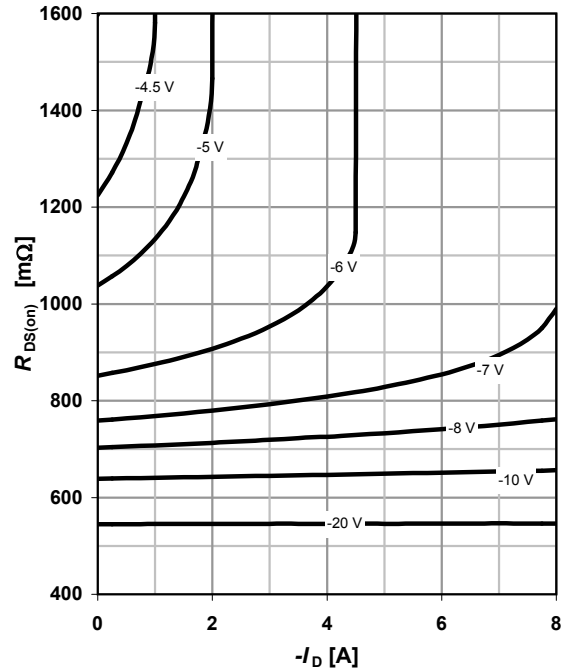


5 Typ. output characteristics

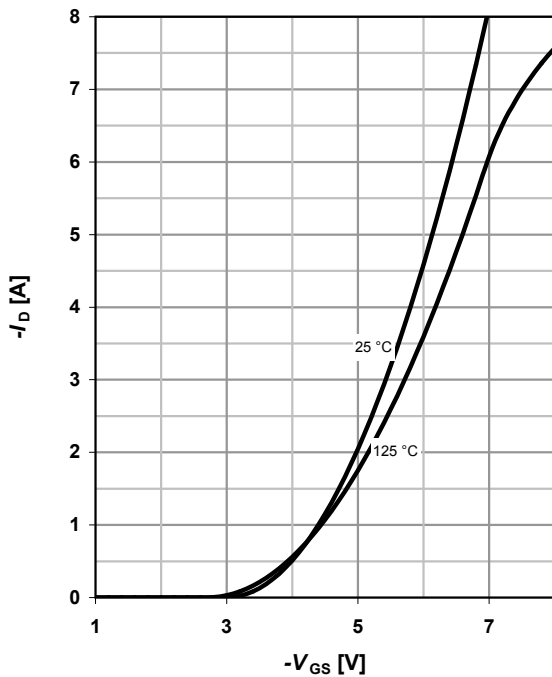
$$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$$

 parameter: V_{GS}

6 Typ. drain-source on resistance

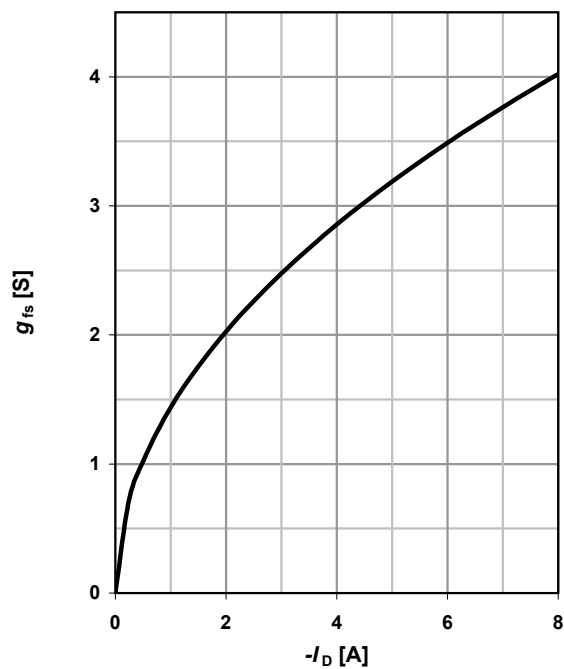
$$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$$

 parameter: V_{GS}

7 Typ. transfer characteristics

$$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$$

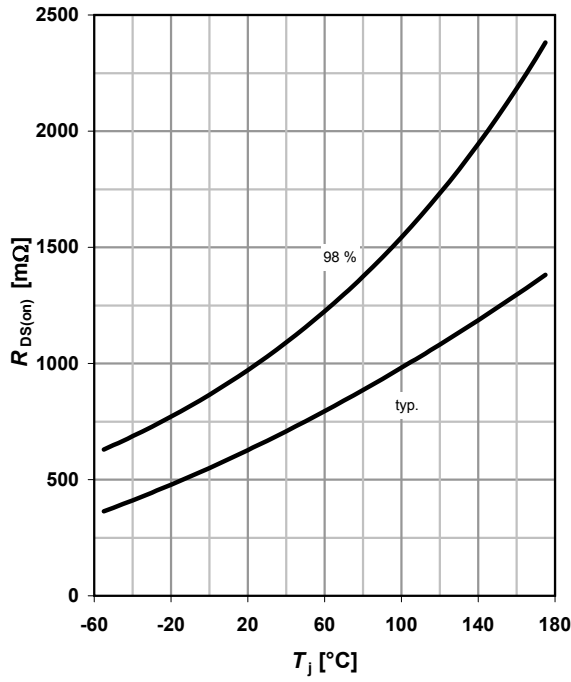
 parameter: T_j

8 Typ. forward transconductance

$$g_{fs} = f(I_D); T_j = 25\text{ }^\circ\text{C}$$



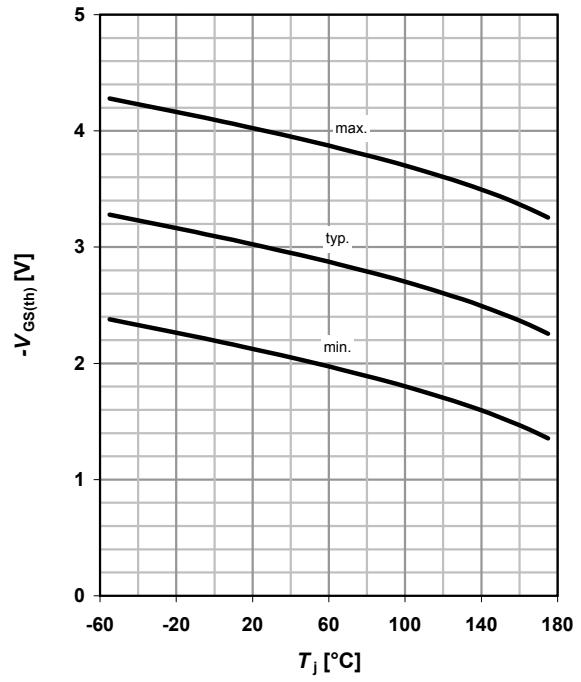
9 Drain-source on-state resistance

$R_{DS(on)} = f(T_j); I_D = -4 \text{ A}; V_{GS} = -10 \text{ V}$



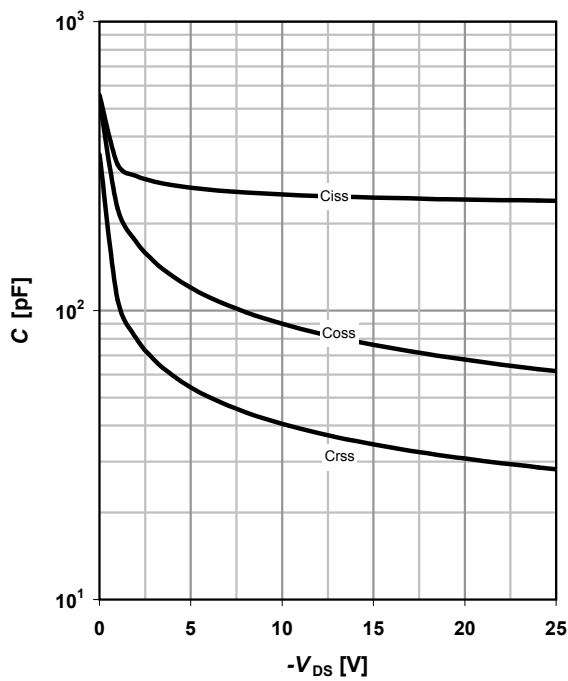
10 Typ. gate threshold voltage

$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}; I_D = -380 \mu\text{A}$



11 Typ. capacitances

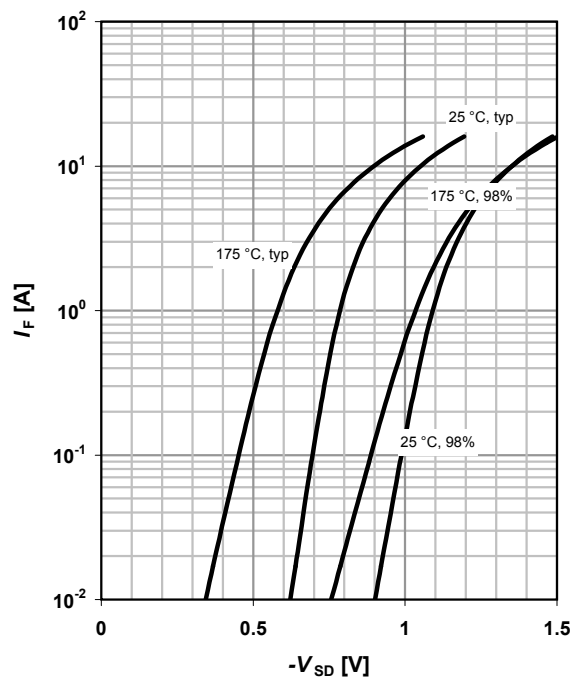
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



12 Forward characteristics of reverse diode

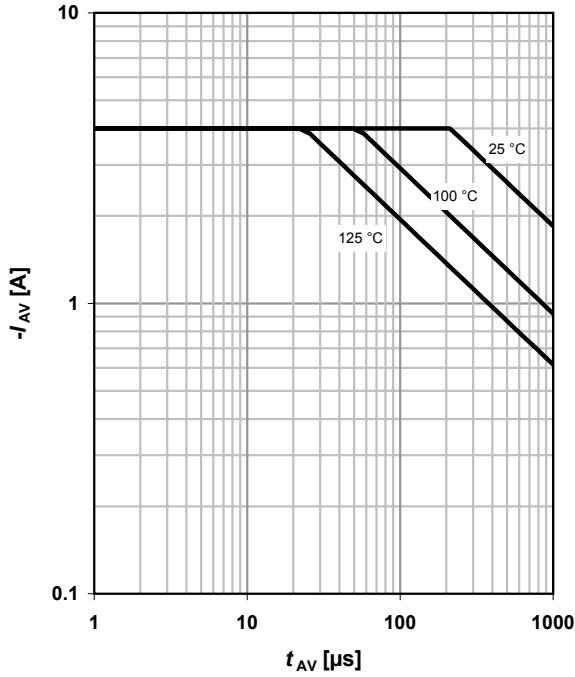
$I_F = f(V_{SD})$

parameter: T_j

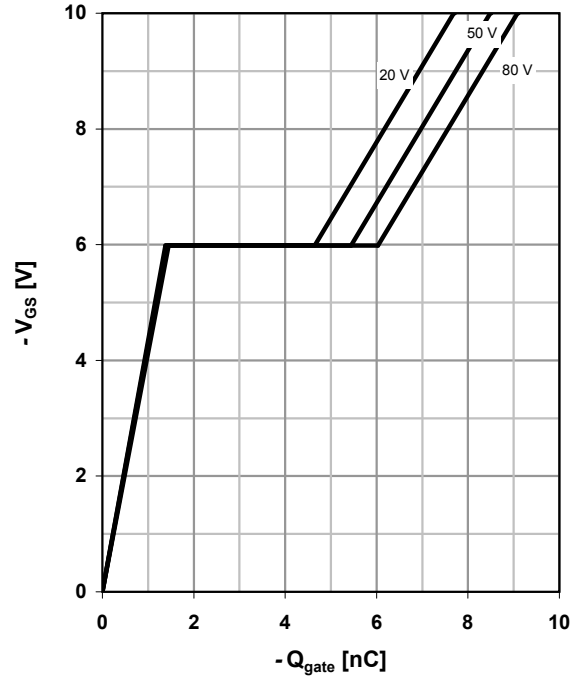


13 Avalanche characteristics

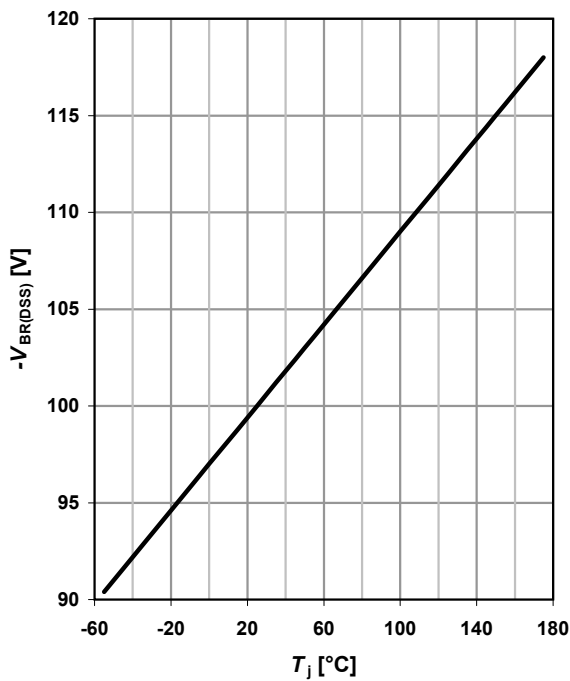
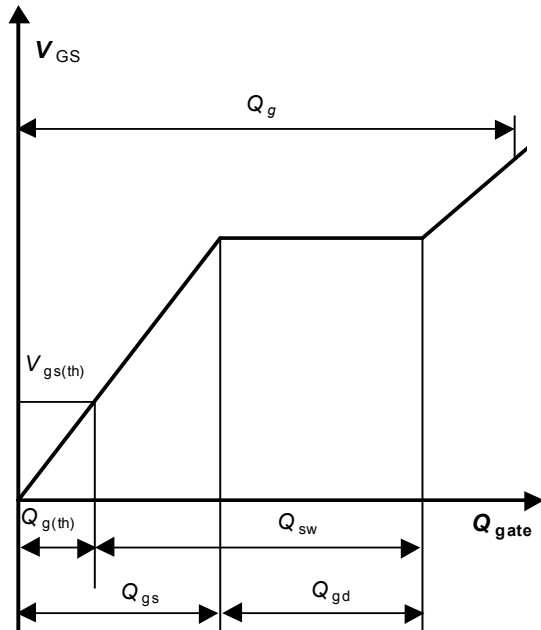
$$I_{AS}=f(t_{AV}); R_{GS}=25\ \Omega$$

 parameter: $T_{j(\text{start})}$

14 Typ. gate charge

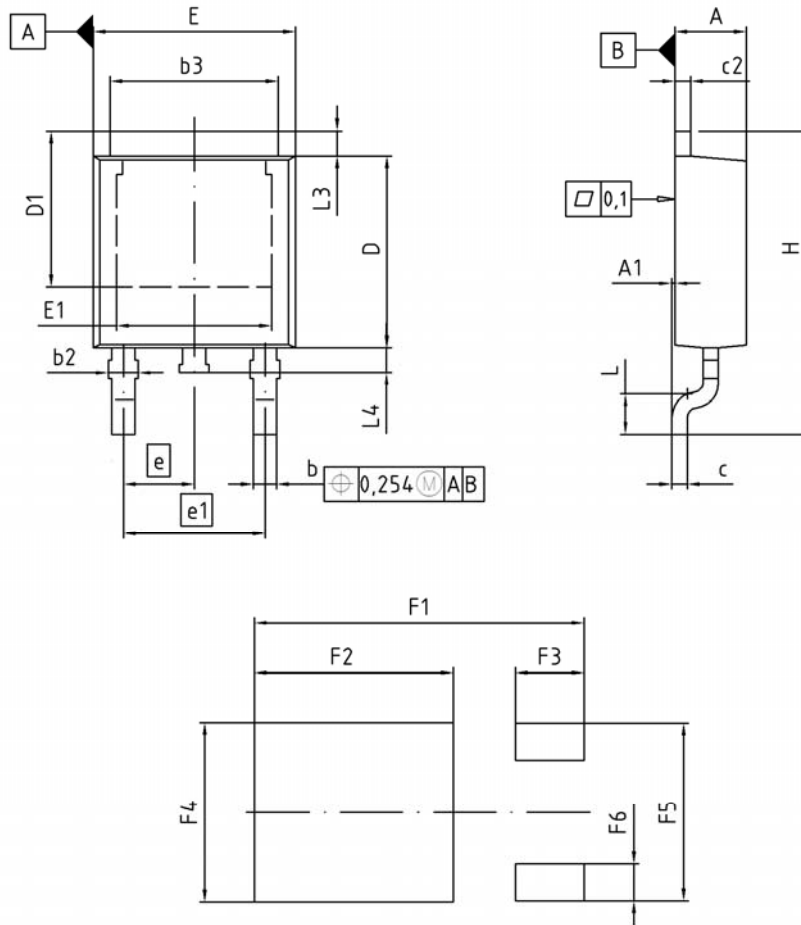
$$V_{GS}=f(Q_{\text{gate}}); I_D=-4\ \text{A pulsed}$$

 parameter: V_{DD}

15 Drain-source breakdown voltage

$$V_{BR(DSS)}=f(T_j); I_D=-250\ \mu\text{A}$$


16 Gate charge waveforms


Package Outline: PG-TO-252-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.16	2.41	0.085	0.095
A1	0.00	0.15	0.000	0.006
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b3	5.00	5.50	0.197	0.217
c	0.46	0.60	0.018	0.024
c2	0.46	0.98	0.018	0.039
D	5.97	6.22	0.235	0.245
D1	5.02	5.84	0.198	0.230
E	6.40	6.73	0.252	0.265
E1	4.70	5.21	0.185	0.205
e	2.29		0.090	
e1	4.57		0.180	
N	3		3	
H	9.40	10.48	0.370	0.413
L	1.18	1.70	0.046	0.067
L3	0.90	1.25	0.035	0.049
L4	0.51	1.00	0.020	0.039
F1	10.50	10.70	0.413	0.421
F2	6.30	6.50	0.248	0.256
F3	2.10	2.30	0.083	0.091
F4	5.70	5.90	0.224	0.232
F5	5.66	5.86	0.223	0.231
F6	1.10	1.30	0.043	0.051

DOCUMENT NO.
Z8B00003328

SCALE

EUROPEAN PROJECTION

ISSUE DATE
19-10-2007

REVISION
03

Published by
Infineon Technologies AG
81726 Munich, Germany
© 2008 Infineon Technologies AG
All Rights Reserved.

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office. Infineon Technologies components may be used in life-support devices or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

单击下面可查看定价，库存，交付和生命周期等信息

[>>Infineon Technologies\(英飞凌\)](#)

[>>点击查看相关商品](#)